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<input type="checkbox"/>	L8	l1 and l2 and l3 and l4 and l5 and l7	14
<input type="checkbox"/>	L7	(heat\$3 or anneal\$3)	325809
<input type="checkbox"/>	L6	(heat43 or anneal\$3)	47889
<input type="checkbox"/>	L5	(barrier adj layer\$)near6 (resist\$3 or immun\$6 r insuscept\$4)	806
<input type="checkbox"/>	L4	L3	771
<input type="checkbox"/>	L3	(Ge or germanium) near4 (surface\$2)	771
<input type="checkbox"/>	L2	(insulator near4 substrate\$)	6461
<input type="checkbox"/>	L1	(Si near2 Ge or SiGe or silicon adj germanium)	11779

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Search Results - Record(s) 1 through 10 of 14 returned.

1. Document ID: US 20050130424 A1

L8: Entry 1 of 14

File: PGPB

Jun 16, 2005

PGPUB-DOCUMENT-NUMBER: 20050130424

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20050130424 A1

TITLE: Use of hydrogen implantation to improve material properties of silicon-germanium-on-insulator material made by thermal diffusion

PUBLICATION-DATE: June 16, 2005

INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
Bedell, Stephen W.	Wappingers Falls	NY	US	
Fogel, Keith E.	Mohegan Lake	NY	US	
Sadana, Devendra K.	Pleasantville	NY	US	

US-CL-CURRENT: 438/689

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Sequences](#) | [Attachments](#) | [Claims](#) | [KAC](#) | [Drawn Obj](#)

2. Document ID: US 20050095803 A1

L8: Entry 2 of 14

File: PGPB

May 5, 2005

PGPUB-DOCUMENT-NUMBER: 20050095803

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20050095803 A1

TITLE: Formation of silicon-germanium-on-insulator (SGOI) by an integral high temperature SIMOX-Ge interdiffusion anneal

PUBLICATION-DATE: May 5, 2005

INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
Bedell, Stephen W.	Wappingers Falls	NY	US	
Fogel, Keith E.	Mohegan Lake	NY	US	
Sadana, Devendra K.	Pleasantville	NY	US	
Shahidi, Ghavam G.	Pound Ridge	NY	US	

US-CL-CURRENT: 438/407[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Sequences](#) | [Attachments](#) | [Claims](#) | [KINIC](#) | [Drawn D](#)**3. Document ID: US 20050093100 A1**

L8: Entry 3 of 14

File: PGPB

May 5, 2005

PGPUB-DOCUMENT-NUMBER: 20050093100

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20050093100 A1

TITLE: Method for fabricating SiGe-on-insulator (SGOI) and Ge-on-insulator (GOI) substrates

PUBLICATION-DATE: May 5, 2005

INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
Chen, Tze-chiang	Yorktown Heights	NY	US	
Cohen, Guy M.	Mohegan Lake	NY	US	
Reznicek, Alexander	Mount Kisco	NY	US	
Sadana, Devendra K.	Pleasantville	NY	US	
Shahidi, Ghavam G.	Pound Ridge	NY	US	

US-CL-CURRENT: 257/616[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Sequences](#) | [Attachments](#) | [Claims](#) | [KINIC](#) | [Drawn D](#)**4. Document ID: US 20050048778 A1**

L8: Entry 4 of 14

File: PGPB

Mar 3, 2005

PGPUB-DOCUMENT-NUMBER: 20050048778

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20050048778 A1

TITLE: Use of thin SOI to inhibit relaxation of SiGe layers

PUBLICATION-DATE: March 3, 2005

INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
Bedell, Stephen W.	Wappingers Falls	NY	US	
Chen, Huajie	Wappingers Falls	NY	US	
Fogel, Keith E.	Mohegan Lake	NY	US	
Sadana, Devendra K.	Pleasantville	NY	US	

US-CL-CURRENT: 438/689; 117/4, 257/E21.129

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KMC	Drawn	Def
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 5. Document ID: US 20050003229 A1

L8: Entry 5 of 14

File: PGPB

Jan 6, 2005

PGPUB-DOCUMENT-NUMBER: 20050003229

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20050003229 A1

TITLE: Defect reduction by oxidation of silicon

PUBLICATION-DATE: January 6, 2005

INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
Bedell, Stephen W.	Wappingers Falls	NY	US	
Chen, Huajie	Wappingers Falls	NY	US	
Domenicucci, Anthony G.	New Paltz	NY	US	
Fogel, Keith E.	Mohegan Lake	NY	US	
Sadana, Devendra K.	Pleasantville	NY	US	

US-CL-CURRENT: 428/641; 257/E21.561, 438/514

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KMC	Drawn	Def
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 6. Document ID: US 20040259334 A1

L8: Entry 6 of 14

File: PGPB

Dec 23, 2004

PGPUB-DOCUMENT-NUMBER: 20040259334

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20040259334 A1

TITLE: High-quality SGOI by annealing near the alloy melting point

PUBLICATION-DATE: December 23, 2004

INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
Bedell, Stephen W.	Wappingers Falls	NY	US	
Chen, Huajie	New Paltz	NY	US	
Domenicucci, Anthony G.	Mohegan Lake	NY	US	
Fogel, Keith E.	Clinton Corners	NY	US	
Murphy, Richard J.	Pleasantville	NY	US	
Sadana, Devendra K.			US	

US-CL-CURRENT: 438/478

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Sequences](#) | [Attachments](#) | [Claims](#) | [KWC](#) | [Drawn D](#)

7. Document ID: US 20040242006 A1

L8: Entry 7 of 14

File: PGPB

Dec 2, 2004

PGPUB-DOCUMENT-NUMBER: 20040242006

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20040242006 A1

TITLE: SiGe lattice engineering using a combination of oxidation, thinning and epitaxial regrowth

PUBLICATION-DATE: December 2, 2004

INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
Bedell, Stephen W.	Wappingers Falls	NY	US	
Chen, Huajie	Wappingers Falls	NY	US	
Fogel, Keith E.	Mohegan lake	NY	US	
Sadana, Devendra K.	Pleasantville	NY	US	

US-CL-CURRENT: 438/692

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Sequences](#) | [Attachments](#) | [Claims](#) | [KWC](#) | [Drawn D](#)

8. Document ID: US 20040241460 A1

L8: Entry 8 of 14

File: PGPB

Dec 2, 2004

PGPUB-DOCUMENT-NUMBER: 20040241460

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20040241460 A1

TITLE: Formation of silicon-Germanium-on-insulator (SGOI) by an integral high temperature SIMOX-Ge interdiffusion anneal

PUBLICATION-DATE: December 2, 2004

INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
Bedell, Stephen W.	Wappingers Falls	NY	US	
de Souza, Joel P.	Putnam Valley	NY	US	
Fogel, Keith E.	Mohegan Lake	NY	US	
Sadana, Devendra K.	Pleasantville	NY	US	
Shahidi, Ghavam G.	Pound Ridge	NY	US	

US-CL-CURRENT: 428/446; 428/450, 428/641, 438/479

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWC	Drawn D
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 9. Document ID: US 20040241459 A1

L8: Entry 9 of 14

File: PGPB

Dec 2, 2004

PGPUB-DOCUMENT-NUMBER: 20040241459

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20040241459 A1

TITLE: Formation of silicon-germanium-on-insulator (SGOI) by an integral high temperature SIMOX-Ge interdiffusion anneal

PUBLICATION-DATE: December 2, 2004

INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
Bedell, Stephen W.	Wappingers Falls	NY	US	
Fogel, Keith E.	Mohegan Lake	NY	US	
Sadana, Devendra K.	Pleasantville	NY	US	
Shahidi, Ghavam G.	Pound Ridge	NY	US	

US-CL-CURRENT: 428/446; 428/641

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWC	Drawn D
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 10. Document ID: US 20040238885 A1

L8: Entry 10 of 14

File: PGPB

Dec 2, 2004

PGPUB-DOCUMENT-NUMBER: 20040238885

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20040238885 A1

TITLE: High-quality SGOI by oxidation near the alloy melting temperature

PUBLICATION-DATE: December 2, 2004

INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
Bedell, Stephen W.	Wappingers Falls	NY	US	
Domenicucci, Anthony G.	New Paltz	NY	US	
Fogel, Keith E.	Mohegan Lake	NY	US	
Sadana, Devendra K.	Pleasantville	NY	US	

US-CL-CURRENT: 257/347

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWC	Drawn D
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Terms	Documents
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Day : Tuesday
 Date: 7/12/2005

Time: 11:28:10

PALM INTRANET

Inventor Name Search Result

Your Search was:

Last Name = FOGEL

First Name = KEITH

Application#	Patent#	Status	Date Filed	Title	Inventor Name 46
60421480	Not Issued	159	10/24/2002	LAND GRID ARRAY FABRICATION USING ELASTOMER CORE AND CONDUCTING METAL SHELL OR MESH	FOGEL, KEITH E.
60026088	Not Issued	159	09/13/1996	WAFER SCALE HIGH DENSITY PROBE ASSEMBLY	FOGEL, KEITH E
60020000	Not Issued	159	06/21/1996	FOAMED ELASTOMERS FOR WAFER PROBING APPLICATIONS AND INTERPOSER CONNECTORS	FOGEL, KEITH E.
11039602	Not Issued	030	01/19/2005	FORMATION OF SILICON-GERMANIUM-ON-INSULATOR (SGOI) BY AN INTEGRAL HIGH TEMPERATURE SIMOX-GE INTERDIFFUSION ANNEAL	FOGEL, KEITH E.
11029921	Not Issued	030	01/05/2005	HIGH-QUALITY SGOI BY OXIDATION NEAR THE ALLOY MELTING TEMPERATURE	FOGEL, KEITH E.
10993270	Not Issued	020	11/19/2004	PATTERNEDE SOI BY OXYGEN IMPLANTATION AND ANNEALING	FOGEL, KEITH E.
10984212	Not Issued	030	11/09/2004	FORMATION OF SILICON-GERMANIUM-ON-INSULATOR (SGOI) BY AN INTEGRAL HIGH TEMPERATURE SIMOX-GE INTERDIFFUSION ANNEAL	FOGEL, KEITH E.
10982411	Not Issued	030	11/05/2004	USE OF HYDROGEN IMPLANTATION TO IMPROVE MATERIAL PROPERTIES OF SILICON-GERMANIUM-ON-INSULATOR MATERIAL MADE BY THERMAL DIFFUSION	FOGEL, KEITH E.

<u>10932598</u>	Not Issued	020	09/02/2004	METHOD OF PRODUCING SILICON-GERMANIUM-ON-INSULATOR MATERIAL USING UNSTRAINED GE-CONTAINING SOURCE LAYERS	FOGEL, KEITH E.
<u>10928473</u>	Not Issued	030	08/27/2004	ELECTRICAL CONNECTOR DESIGN AND CONTACT GEOMETRY AND METHOD OF USE THEREOF AND METHODS OF FABRICATION THEREOF	FOGEL, KEITH
<u>10890765</u>	Not Issued	030	07/14/2004	ION IMPLANTATION FOR SUPPRESSION OF DEFECTS IN ANNEALED SIGE LAYERS	FOGEL, KEITH E.
<u>10883887</u>	Not Issued	030	07/02/2004	STRAINED SILICON-ON-INSULATOR BY ANODIZATION OF A BURIED P+ SILICON GERMANIUM LAYER	FOGEL, KEITH E.
<u>10883883</u>	Not Issued	041	07/02/2004	ULTRA-THIN, HIGH QUALITY STRAINED SILICON-ON-INSULATOR FORMED BY ELASTIC STRAIN TRANSFER	FOGEL, KEITH E.
<u>10855915</u>	Not Issued	041	05/27/2004	HIGH-QUALITY SGOI BY ANNEALING NEAR THE ALLOY MELTING POINT	FOGEL, KEITH E.
<u>10824289</u>	Not Issued	030	04/14/2004	METHOD OF CREATING HIGH-QUALITY RELAXED SIGE-ON-INSULATOR FOR STRAINED SI CMOS APPLICATIONS	FOGEL, KEITH E.
<u>10818572</u>	Not Issued	030	04/06/2004	METHOD OF FORMING HIGH-QUALITY RELAXED SIGE ALLOY LAYERS ON BULK SI SUBSTRATES	FOGEL, KEITH E.
<u>10815103</u>	Not Issued	030	03/31/2004	INTERCONNECTIONS FOR FLIP-CHIP USING LEAD-FREE SOLDERS AND HAVING REACTION BARRIER LAYERS	FOGEL, KEITH E.
<u>10768341</u>	Not Issued	030	01/30/2004	HIGH ELECTRICAL QUALITY BURIED OXIDE IN SIMOX	FOGEL, KEITH E.
<u>10715288</u>	Not Issued	061	11/17/2003	INTERPOSER WITH ELECTRICAL CONTACT BUTTON AND METHOD	FOGEL, KEITH E.
<u>10710826</u>	Not Issued	030	08/05/2004	METHOD OF FORMING STRAINED SILICON MATERIALS WITH IMPROVED	FOGEL, KEITH

THERMAL CONDUCTIVITY				
<u>10696601</u>	6861158	150	10/29/2003	FORMATION OF SILICON-GERMANIUM-ON-INSULATOR (SGOI) BY AN INTEGRAL HIGH TEMPERATURE SIMOX-GE INTERDIFFUSION ANNEAL
<u>10674648</u>	Not Issued	030	09/30/2003	SOI BY OXIDATION OF POROUS SILICON
<u>10674647</u>	Not Issued	030	09/30/2003	THIN BURIED OXIDES BY LOW-DOSE OXYGEN IMPLANTATION INTO MODIFIED SILICON
<u>10664714</u>	6825102	150	09/18/2003	METHOD OF IMPROVING THE QUALITY OF DEFECTIVE SEMICONDUCTOR MATERIAL
<u>10662028</u>	Not Issued	030	09/12/2003	FORMATION OF A SILICON GERMANIUM-ON-INSULATOR STRUCTURE BY OXIDATION OF A BURIED POROUS SILICON LAYER
<u>10654232</u>	Not Issued	071	09/03/2003	USE OF THIN SOI TO INHIBIT RELAXATION OF SIGE LAYERS
<u>10654231</u>	6803240	150	09/03/2003	METHOD OF MEASURING CRYSTAL DEFECTS IN THIN SI/SIGE BILAYERS
<u>10610612</u>	Not Issued	030	07/01/2003	DEFECT REDUCTION BY OXIDATION OF SILICON
<u>10448954</u>	Not Issued	041	05/30/2003	SIGE LATTICE ENGINEERING USING A COMBINATION OF OXIDATION, THINNING AND EPITAXIAL REGROWTH
<u>10448948</u>	Not Issued	041	05/30/2003	HIGH-QUALITY SGOI BY OXIDATION NEAR THE ALLOY MELTING TEMPERATURE
<u>10448947</u>	6855436	150	05/30/2003	FORMATION OF SILICON-GERMANIUM-ON-INSULATOR (SGOI) BY AN INTEGRAL HIGH TEMPERATURE SIMOX-GE INTERDIFFUSION ANNEAL
<u>10341819</u>	6717217	150	01/14/2003	ULTIMATE SIMOX
<u>10336147</u>	6878611	150	01/02/2003	PATTERNED STRAINED SILICON FOR HIGH

PERFORMANCE CIRCUITS					
<u>10334220</u>	6800518	150	12/30/2002	FORMATION OF PATTERNED SILICON-ON-INSULATOR (SOI)/SILICON-ON-NOTHING (SON) COMPOSITE STRUCTURE BY POROUS SI ENGINEERING	FOGEL, KEITH E.
<u>10300189</u>	Not Issued	092	11/20/2002	RELAXED, LOW-DEFECT SGOI FOR STRAINED SI CMOS APPLICATIONS	FOGEL, KEITH E.
<u>10196611</u>	6841457	150	07/16/2002	USE OF HYDROGEN IMPLANTATION TO IMPROVE MATERIAL PROPERTIES OF SILICON-GERMANIUM-ON-INSULATOR MATERIAL MADE BY THERMAL DIFFUSION	FOGEL, KEITH E.
<u>10055138</u>	6805962	150	01/23/2002	METHOD OF CREATING HIGH-QUALITY RELAXED SIGE-ON-INSULATOR FOR STRAINED SI CMOS APPLICATIONS	FOGEL, KEITH E.
<u>09861596</u>	6541356	150	05/21/2001	THE ULTIMATE SIMOX	FOGEL, KEITH E.
<u>09861590</u>	6846727	150	05/21/2001	PATTERNED SOI BY OXYGEN IMPLANTATION AND ANNEALING	FOGEL, KEITH E.
<u>09251988</u>	Not Issued	092	02/17/1999	STRUCTURAL DESIGN AND PROCESSES TO CONTROL PROBE POSITION ACCURACY IN A WAFER TEST PROBE ASSEMBLY	FOGEL, KEITH E.
<u>09081342</u>	6525551	150	05/19/1998	PROBE STRUCTURES FOR TESTING ELECTRICAL INTERCONNECTIONS TO INTEGRATED CIRCUIT ELECTRONIC DEVICES	FOGEL, KEITH EDWARD
<u>08425639</u>	Not Issued	161	04/20/1995	HIGH TEMPERATURE CHIP TEST PROBE	FOGEL, KEITH E.
<u>08425543</u>	Not Issued	161	04/20/1995	HIGH DENSITY INTEGRAL TEST PROBE AND FABRICATION METHOD	FOGEL, KEITH E.
<u>08224383</u>	Not Issued	166	04/07/1994	INTEGRAL RIGID CHIP TEST PROBE	FOGEL, KEITH E.
<u>07485016</u>	4975079	250	02/23/1990	CONNECTOR ASSEMBLY FOR CHIP TESTING	FOGEL, KEITH

Inventor Search Completed: No Records to Display.

Day : Tuesday
Date: 7/12/2005

Time: 11:27:35

PALM INTRANET**Inventor Name Search Result**

Your Search was:

Last Name = BEDELL

First Name = STEPHEN

Application#	Patent#	Status	Date Filed	Title	Inventor Name 48
<u>60236549</u>	Not Issued	159	09/29/2000	METHOD OF TRANSPORTING HYDROGEN TO SUB-SURFACE REGION OR CRYSTALLINE INTERFACE WHILE MINIMIZING LATTICE DAMAGE	BEDELL, STEPHEN W.
<u>10982411</u>	Not Issued	030	11/05/2004	USE OF HYDROGEN IMPLANTATION TO IMPROVE MATERIAL PROPERTIES OF SILICON-GERMANIUM-ON-INSULATOR MATERIAL MADE BY THERMAL DIFFUSION	BEDELL, STEPHEN W.
<u>10943354</u>	Not Issued	041	09/17/2004	METHOD FOR PREVENTING SIDEWALL CONSUMPTION DURING OXIDATION OF SGOI ISLANDS	BEDELL, STEPHEN W.
<u>10932598</u>	Not Issued	020	09/02/2004	METHOD OF PRODUCING SILICON-GERMANIUM-ON-INSULATOR MATERIAL USING UNSTRAINED GE-CONTAINING SOURCE LAYERS	BEDELL, STEPHEN W.
<u>10905477</u>	Not Issued	030	01/06/2005	METHOD OF CREATING A GE-RICH CHANNEL LAYER FOR HIGH-PERFORMANCE CMOS CIRCUITS	BEDELL, STEPHEN W.
<u>10890765</u>	Not Issued	030	07/14/2004	ION IMPLANTATION FOR SUPPRESSION OF DEFECTS IN ANNEALED SIGE LAYERS	BEDELL, STEPHEN W.
<u>10883887</u>	Not Issued	030	07/02/2004	STRAINED SILICON-ON-INSULATOR BY ANODIZATION OF A BURIED P+ SILICON GERMANIUM LAYER	BEDELL, STEPHEN W.

<u>10883883</u>	Not Issued	041	07/02/2004	ULTRA-THIN, HIGH QUALITY STRAINED SILICON-ON-INSULATOR FORMED BY ELASTIC STRAIN TRANSFER	BEDELL, STEPHEN W.
<u>10855915</u>	Not Issued	041	05/27/2004	HIGH-QUALITY SGOI BY ANNEALING NEAR THE ALLOY MELTING POINT	BEDELL, STEPHEN W.
<u>10710826</u>	Not Issued	030	08/05/2004	METHOD OF FORMING STRAINED SILICON MATERIALS WITH IMPROVED THERMAL CONDUCTIVITY	BEDELL, STEPHEN W.
<u>10710255</u>	6893936	150	06/29/2004	METHOD OF FORMING STRAINED SI/SIGE ON INSULATOR WITH SILICON GERMANIUM BUFFER	BEDELL, STEPHEN W.
<u>10685636</u>	Not Issued	041	10/15/2003	TECHNIQUES FOR LAYER TRANSFER PROCESSING	BEDELL, STEPHEN W.
<u>10664714</u>	6825102	150	09/18/2003	METHOD OF IMPROVING THE QUALITY OF DEFECTIVE SEMICONDUCTOR MATERIAL	BEDELL, STEPHEN W.
<u>10662028</u>	Not Issued	030	09/12/2003	FORMATION OF A SILICON GERMANIUM-ON-INSULATOR STRUCTURE BY OXIDATION OF A BURIED POROUS SILICON LAYER	BEDELL, STEPHEN W.
<u>10654232</u>	Not Issued	071	09/03/2003	USE OF THIN SOI TO INHIBIT RELAXATION OF SIGE LAYERS	BEDELL, STEPHEN W.
<u>10654231</u>	6803240	150	09/03/2003	METHOD OF MEASURING CRYSTAL DEFECTS IN THIN SI/SIGE BILAYERS	BEDELL, STEPHEN W.
<u>10604989</u>	6875982	150	08/29/2003	AN ELECTRON MICROSCOPE MAGNIFICATION STANDARD PROVIDING PRECISE CALIBRATION IN THE MAGNIFICATION RANGE 5000X-2000,000X	BEDELL, STEPHEN W.
<u>10448947</u>	6855436	150	05/30/2003	FORMATION OF SILICON-GERMANIUM-ON-INSULATOR (SGOI) BY AN INTEGRAL HIGH TEMPERATURE SIMOX-GE INTERDIFFUSION ANNEAL	BEDELL, STEPHEN W.
<u>10336147</u>	6878611	150	01/02/2003	PATTERNE STRAINED SILICON FOR HIGH PERFORMANCE CIRCUITS	BEDELL, STEPHEN W.

<u>10300189</u>	Not Issued	092	11/20/2002	RELAXED, LOW-DEFECT SGOI FOR STRAINED Si CMOS APPLICATIONS	BEDELL, STEPHEN W.
<u>10196611</u>	6841457	150	07/16/2002	USE OF HYDROGEN IMPLANTATION TO IMPROVE MATERIAL PROPERTIES OF SILICON-GERMANIUM-ON-INSULATOR MATERIAL MADE BY THERMAL DIFFUSION	BEDELL, STEPHEN W.
<u>08816012</u>	5922109	150	03/11/1997	GAS DRYING PROCESS USING GLYCOL SOLUTION SOLUBILITY SUPPRESSANTS	BEDELL, STEPHEN A.
<u>08360890</u>	Not Issued	164	12/21/1994	OXALATE CONTROL	BEDELL, STEPHEN A.
<u>08179882</u>	5433934	150	01/11/1994	METHOD FOR SIMULTANEOUS ABSORPTION OF SULFUR DIOXIDE AND NITRIC OXIDE FROM FLUE GAS	BEDELL, STEPHEN A.
<u>07964323</u>	5320816	150	10/21/1992	PROCESS FOR ABSORPTION OF SULFUR DIOXIDE AND NITRIC OXIDE FROM FLUE GAS	BEDELL, STEPHEN A.
<u>07744157</u>	Not Issued	166	08/13/1991	COMPOSITION AND METHOD FOR SIMULTANEOUS ABSORPTION OF SULFUR DIOXIDE AND NITRIC OXIDE	BEDELL, STEPHEN A.
<u>07623313</u>	5167941	150	12/06/1990	QUATERNARY POLYAMINES AS SULFITE OXIDATION INHIBITORS IN AMINE SCRUBBING OF SO₂	BEDELL, STEPHEN A.
<u>07592402</u>	5338778	150	10/03/1990	REMOVAL OF HYDROGEN SULFIDE FROM FLUID STREAMS	BEDELL, STEPHEN A.
<u>07578114</u>	5043504	150	09/05/1990	INHIBITION OF BUTADIENE-POLYMERIZATION DURING THE CONVERSION OF BUTADIENE TO VINYL CYCLOHEXENE	BEDELL, STEPHEN A.
<u>07546075</u>	5019365	150	06/29/1990	QUATERNARY POLYAMINES AS SULFITE OXIDATION INHIBITORS	BEDELL, STEPHEN A.
<u>07368613</u>	4921683	150	06/20/1989	NITRIC OXIDE ABATEMENT WITH POLYMERIC COBALT (III) CHELATES	BEDELL, STEPHEN A.
<u>07359896</u>	4960576	150	06/01/1989	H₂S ABATEMENT IN	BEDELL,

				GEOTHERMAL STEAM DURING STACKING OPERATIONS	STEPHEN A.
<u>07359533</u>	4960575	150	06/01/1989	REMOVAL OF HYDROGEN SULFIDE WITH ON SITE GENERATED SULFITE FROM GEOTHERMAL	BEDELL, STEPHEN A.
<u>07295311</u>	5096691	150	01/09/1989	H2S ABATEMENT WITH STABILIZED CHELATES IN GEOTHERMAL DRILLING	BEDELL, STEPHEN A.
<u>07277159</u>	Not Issued	164	11/29/1988	QUATERNARY-POLYAMINES AS SULFITE OXIDATION INHIBITORS	BEDELL, STEPHEN A.
<u>07238024</u>	Not Issued	168	08/29/1988	REMOVAL OF HYDROGEN SULFIDE FROM FLUID STREAMS	BEDELL, STEPHEN A.
<u>07149778</u>	4814051	150	01/29/1988	PROCESS FOR THE RECOVERY OF ALKANOLAMINES FROM THEIR HEAT-STABLE SALTS FORMED IN ALKANOLAMINE SORBENT SOLUTIONS	BEDELL, STEPHEN A.
<u>07149777</u>	4808284	150	01/29/1988	PROCESS FOR THE RECOVERY OF ALKANOLAMINES FROM THEIR HEAT-STABLE SALTS FORMED DURING ABSORBENT THERMAL REGENERATIVE STEP OF GAS CONDITIONING PROCESSES	BEDELL, STEPHEN A.
<u>07121437</u>	Not Issued	161	11/17/1987	DRILLING OIL/GAS WELLS WITH REMOVAL OF H2S	BEDELL, STEPHEN A.
<u>07065449</u>	Not Issued	161	06/23/1987	DRILLING GEOTHERMAL WELLS WITH REMOVAL OF H2S	BEDELL, STEPHEN A.
<u>06924710</u>	Not Issued	161	10/30/1986	DRILLING GEOTHERMAL WELLS WITH REMOVAL OF H2S	BEDELL, STEPHEN A.
<u>06831969</u>	4891205	150	02/24/1986	STABILIZED CHELATING AGENTS FOR REMOVING HYDROGEN SULFIDE	BEDELL, STEPHEN A.
<u>06807428</u>	4623707	150	12/10/1985	POLYMERIZATION OF OLEFINS IN THE PRESENCE OF POLYMER SUPPORTED ZIEGLER-NATTA CATALYSTS	BEDELL, STEPHEN A.
<u>06807419</u>	4632912	150	12/10/1985	POLYMER SUPPORTED ZIEGLER-NATTA CATALYSTS	BEDELL, STEPHEN A.
<u>06805672</u>	4643886	150	12/06/1985	AUTOMATIC PH CONTROL IN	BEDELL,

				A PROCESS FOR REMOVAL OF HYDROGEN SULFIDE FROM A GAS	STEPHEN A.
06802138	4696802	150	11/27/1985	DRILLING GEOTHERMAL WELLS WITH REMOVAL OF H2S	BEDELL, STEPHEN A.
06801255	Not Issued	161	11/25/1985	DRILLING GEOTHERMAL WELLS WITH REMOVAL OF H2S	BEDELL, STEPHEN A.

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Your Search was:

Last Name = CHEN

First Name = HUAJIE

Application#	Patent#	Status	Date Filed	Title	Inventor Name 35
<u>11081271</u>	Not Issued	030	03/16/2005	METHOD OF MAKING STRAINED SEMICONDUCTOR TRANSISTORS HAVING LATTICE-MISMATCHED SEMICONDUCTOR REGIONS UNDERLYING SOURCE AND DRAIN REGIONS	CHEN, HUAJIE
<u>11037622</u>	Not Issued	030	01/18/2005	STRUCTURE AND METHOD FOR MANUFACTURING STRAINED SILICON DIRECTLY-ON-INSULATOR SUBSTRATE WITH HYBRID CRYSTALLINE ORIENTATION AND DIFFERENT STRESS LEVELS	CHEN, HUAJIE
<u>10969718</u>	Not Issued	020	10/20/2004	SELF-ALIGNED MASK FORMED UTILIZING DIFFERENTIAL OXIDATION RATES OF MATERIALS	CHEN, HUAJIE
<u>10943048</u>	Not Issued	030	09/16/2004	BUFFER LAYER FOR SELECTIVE SIGE GROWTH FOR UNIFORM NUCLEATION	CHEN, HUAJIE
<u>10908394</u>	Not Issued	030	05/10/2005	EMBEDDED SILICON GERMANIUM USING A DOUBLE-BURIED OXIDE SILICON-ON-INSULATOR WAFER	CHEN, HUAJIE
<u>10905978</u>	Not Issued	020	01/28/2005	STRUCTURE AND METHOD FOR MANUFACTURING PLANAR STRAINED SI/SIGE SUBSTRATE WITH MULTIPLE ORIENTATIONS AND DIFFERENT STRESS LEVELS	CHEN, HUAJIE
<u>10905598</u>	Not	030	01/12/2005	IN SITU DOPED EMBEDDED	CHEN, HUAJIE

	Issued			SIGE EXTENSION AND SOURCE/DRAIN FOR ENHANCED PFET PERFORMANCE	
<u>10905595</u>	Not Issued	030	01/12/2005	LOW CONCENTRATION SIGE BUFFER DURING STRAINED SI GROWTH OF SSGOI MATERIAL FOR DOPANT DIFFUSION CONTROL AND DEFECT REDUCTION	CHEN, HUAJIE
<u>10890765</u>	Not Issued	030	07/14/2004	ION IMPLANTATION FOR SUPPRESSION OF DEFECTS IN ANNEALED SIGE LAYERS	CHEN, HUAJIE
<u>10855915</u>	Not Issued	041	05/27/2004	HIGH-QUALITY SGOI BY ANNEALING NEAR THE ALLOY MELTING POINT	CHEN, HUAJIE
<u>10818572</u>	Not Issued	030	04/06/2004	METHOD OF FORMING HIGH-QUALITY RELAXED SIGE ALLOY LAYERS ON BULK SI SUBSTRATES	CHEN, HUAJIE
<u>10795672</u>	6916698	150	03/08/2004	HIGH PERFORMANCE CMOS DEVICE STRUCTURE WITH MID-GAP METAL GATE	CHEN, HUAJIE
<u>10751208</u>	Not Issued	092	01/02/2004	METHOD OF PREVENTING SURFACE ROUGHENING DURING HYDROGEN PREBAKE OF SIGE SUBSTRATES	CHEN, HUAJIE
<u>10751207</u>	Not Issued	041	01/02/2004	METHOD OF PREVENTING SURFACE ROUGHENING DURING HYDROGEN PREBAKE OF SIGE SUBSTRATES USING CHLORINE CONTAINING GASES	CHEN, HUAJIE
<u>10728519</u>	Not Issued	093	12/05/2003	METHOD OF FABRICATING STRAINED Si-SOI WAFERS	CHEN, HUAJIE
<u>10711899</u>	Not Issued	041	10/12/2004	ULTRA SHALLOW JUNCTION FORMATION BY EPITAXIAL INTERFACE LIMITED DIFFUSION	CHEN, HUAJIE
<u>10711637</u>	Not Issued	030	09/29/2004	STRUCTURE AND METHOD FOR MAKING STRAINED CHANNEL FIELD EFFECT TRANSISTOR USING SACRIFICIAL SPACER	CHEN, HUAJIE
<u>10710826</u>	Not	030	08/05/2004	METHOD OF FORMING	CHEN, HUAJIE

	Issued			STRAINED SILICON MATERIALS WITH IMPROVED THERMAL CONDUCTIVITY	
<u>10710737</u>	Not Issued	030	07/30/2004	CHEMICAL TREATMENT TO RETARD DIFFUSION IN A SEMICONDUCTOR OVERLAYER	CHEN, HUAJIE
<u>10710255</u>	6893936	150	06/29/2004	METHOD OF FORMING STRAINED SI/SIGE ON INSULATOR WITH SILICON GERMANIUM BUFFER	CHEN, HUAJIE
<u>10709239</u>	Not Issued	030	04/23/2004	STRUCTURES AND METHODS FOR MANUFACTURING OF DISLOCATION FREE STRESSED CHANNELS IN BULK SILICON AND SOI CMOS DEVICES BY GATE STRESS ENGINEERING WITH SIGE AND/OR SI:C	CHEN, HUAJIE
<u>10708378</u>	Not Issued	041	02/27/2004	HYBRID SOI/BULK SEMICONDUCTOR TRANSISTORS	CHEN, HUAJIE
<u>10689506</u>	Not Issued	041	10/20/2003	HIGH PERFORMANCE STRESS-ENHANCED MOSFETS USING SI:C AND SIGE EPITAXIAL SOURCE/DRAIN AND METHOD OF MANUFACTURE	CHEN, HUAJIE
<u>10654232</u>	Not Issued	071	09/03/2003	USE OF THIN SOI TO INHIBIT RELAXATION OF SIGE LAYERS	CHEN, HUAJIE
<u>10610612</u>	Not Issued	030	07/01/2003	DEFECT REDUCTION BY OXIDATION OF SILICON	CHEN, HUAJIE
<u>10605134</u>	6906360	150	09/10/2003	STRUCTURE AND METHOD OF MAKING STRAINED CHANNEL CMOS TRANSISTORS HAVING LATTICE-MISMATCHED EPITAXIAL EXTENSION AND SOURCE AND DRAIN REGIONS	CHEN, HUAJIE
<u>10604907</u>	Not Issued	095	08/26/2003	THIN CHANNEL FET WITH RECESSED SOURCE/DRAINS AND EXTENSIONS	CHEN, HUAJIE
<u>10604607</u>	6891192	150	08/04/2003	STRUCTURE AND METHOD OF MAKING STRAINED SEMICONDUCTOR CMOS	CHEN, HUAJIE

				TRANSISTORS HAVING LATTICE MISMATCHED SEMICONDUCTOR REGIONS UNDERLYING SOURCE AND DRAIN REGIONS	
<u>10448954</u>	Not Issued	041	05/30/2003	SIGE LATTICE ENGINEERING USING A COMBINATION OF OXIDATION, THINNING AND EPITAXIAL REGROWTH	CHEN, HUAJIE
<u>10345469</u>	6844225	150	01/15/2003	SELF-ALIGNED MASK FORMED UTILIZING DIFFERENTIAL OXIDATION RATES OF MATERIALS	CHEN, HUAJIE
<u>10250181</u>	6749684	150	06/10/2003	METHOD FOR IMPROVING CVD FILM QUALITY UTILIZING POLYSILICON GETTERER	CHEN, HUAJIE
<u>10250100</u>	6777302	150	06/04/2003	NITRIDE PEDESTAL FOR RAISED EXTRINSIC BASE HBT PROCESS	CHEN, HUAJIE
<u>10249563</u>	6780695	150	04/18/2003	BICMOS INTEGRATION SCHEME WITH RAISED EXTRINSIC BASE	CHEN, HUAJIE
<u>10127196</u>	6762469	150	04/19/2002	HIGH PERFORMANCE CMOS DEVICE STRUCTURE WITH MID-GAP METAL GATE	CHEN, HUAJIE

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